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With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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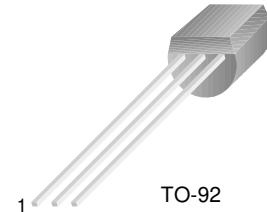


2N5772

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NPN Switching Transistor

- Sourced from process 22.



TO-92
1. Emitter 2. Base 3. Collector

Absolute Maximum Ratings * $T_a=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	15	V
V_{CBO}	Collector-Base Voltage	40	V
V_{EBO}	Emitter-Base Voltage	5.0	V
I_C	Collector Current - Continued	300	mA
T_{STG}	Operating and Storage Junction Temperature Range	- 55 ~ 150	$^\circ\text{C}$

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired

NOTES:

- These ratings are based on a maximum junction temperature of 150 degrees C.
- These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations

Electrical Characteristics $T_a=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
Off Characteristics					
$BV_{(BR)CEO}$	Collector-Emitter Breakdown Voltage *	$I_C = 10\text{mA}, I_B = 0$	15		V
$BV_{(BR)CES}$	Collector-Emitter Breakdown Voltage	$I_C = 100\mu\text{A}, V_{BE} = 0$	40		V
$BV_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 100\mu\text{A}, I_E = 0$	40		V
$BV_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 100\mu\text{A}, I_C = 0$	5.0		V
I_{CBO}	Collector Cutoff Current	$V_{CB} = 20\text{V}, I_E = 0$		0.5	μA
I_{CES}	Collector Cutoff Current	$V_{CE} = 20\text{V}, V_{BE} = 0$ $V_{CE} = 20\text{V}, V_{BE} = 0, T_a = 65^\circ\text{C}$		0.5 3.0	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = 5.0\text{V}, I_C = 0$		100	μA
On Characteristics *					
h_{FE}	DC Current Gain	$V_{CE} = 0.4\text{V}, I_C = 30\text{mA}$ $V_{CE} = 0.5\text{V}, I_C = 100\text{mA}$ $V_{CE} = 1.0\text{V}, I_C = 300\text{mA}$	30 25 15	120	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 30\text{mA}, I_B = 3.0\text{mA}$ $I_C = 100\text{mA}, I_B = 10\text{mA}$ $I_C = 300\text{mA}, I_B = 3.0\text{mA}$		0.2 0.28 0.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 30\text{mA}, I_B = 3.0\text{mA}$ $I_C = 100\text{mA}, I_B = 10\text{mA}$ $I_C = 300\text{mA}, I_B = 3.0\text{mA}$	0.73	0.95 1.2 1.7	V
Small Signal Characteristics					
C_{cb}	Collector-Base Capacitance	$V_{CB} = 5.0\text{V}, I_E = 0, f = 1\text{MHz}$		5.0	pF
C_{eb}	Emitter-Base Capacitance	$V_{CB} = 5.0\text{V}, I_C = 0, f = 1\text{MHz}$		8.0	pF
h_{fe}	Small-Signal Current Gain	$I_C = 300\text{mA}, V_{CE} = 10\text{V}, f = 100\text{MHz}$	3.5		

* Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2.0\%$

Electrical Characteristics $T_a=25^\circ\text{C}$ unless otherwise noted (Continued)

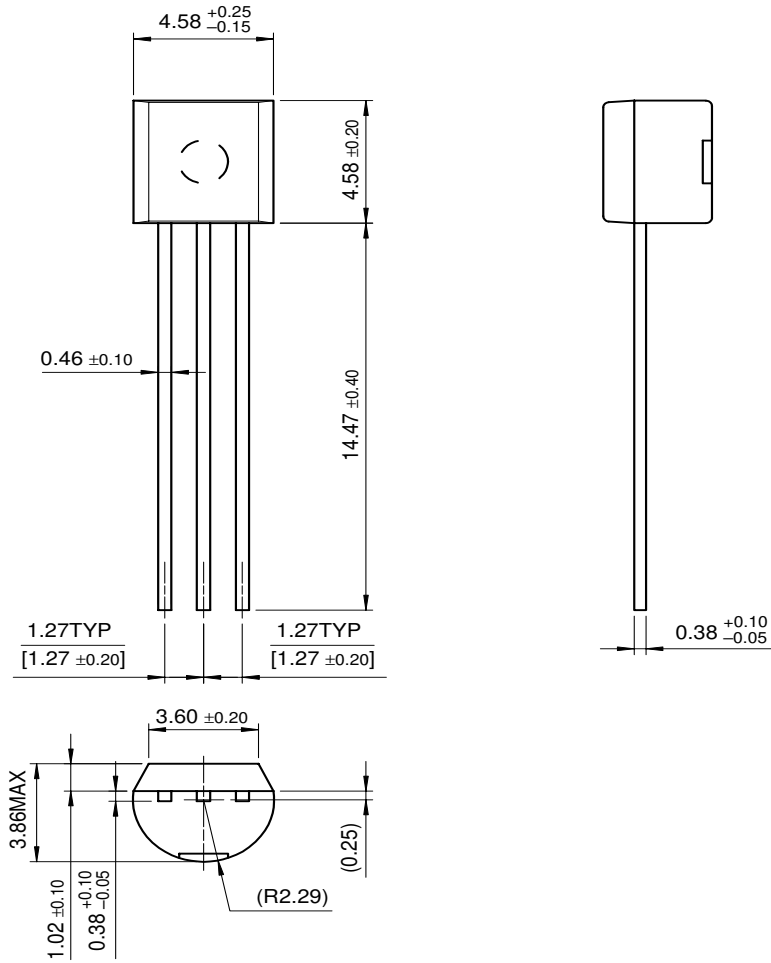
Symbol	Parameter	Test Condition	Min.	Max.	Units
Switching Characteristics					
t_s	Storage Time	$I_C = 300\text{mA}$, $V_{CC} = 10\text{V}$ $I_{B1} = I_{B2} = 30\text{mA}$		20	ns
t_{on}	Turn-On Time			18	ns
t_{off}	Turn-Off Time			28	ns

Thermal Characteristics $T_a=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Max.	Units
P_D	Total Device Dissipation	350	mW
	Derate above 25°C	2.8	mW/ $^\circ\text{C}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	$^\circ\text{C}/\text{W}$

Package Dimensions

TO-92



Dimensions in Millimeters

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